Diode Semiconductor Device - Page 1 of 1



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Inclosure Materia	I:
Metal	
Overall Length:	
Between 0.300 inc	hes and 0.405 inches
Overall Diameter:	
Between 0.255 inc	hes and 0.424 inches
Mounting Facility	Quantity:
1	
Electrode Interna	Ily-electrically Connected To Case:
Cathode	
Mounting Method	l:
Threaded stud	
Features Provide	d:
Hermetically seale	d case
Thread Size:	
0.190 inches	
Semiconductor M	laterial:
Silicon	
Voltage Rating In	Volts Per Characteristic:
120.0 regulator vo	oltage
Current Rating Pe	er Characteristic:
20.00 milliamperes	s repetitive peak forward current
Power Rating Per	Characteristic:
10.0 watts small-si	ignal input power, common-collector
Maximum Operat	ing Tempurature Per Measurement Point:
175.0 degrees cels	sius case
Test Data Docum	ent:
81349-mil-s-19500) specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes of	commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and	performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series De	signator:
Unf	
Terminal Type An	Id Quantity:
1 tab, solder lug a	nd 1 threaded stud
Specification Dat	a:
81349-mil-s-19500	0/124 government specification
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
No	
Fiig:	
A110a0	